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November 2013

RHRP3060

30 A, 600 V Hyperfast Diodes

Features

- Hyperfast Recovery trr = 45 ns (@ IF = 30 A)
- Max Forward Voltage, V_F = 2.1 V (@ T_C = 25°C)
- 600 V Reverse Voltage and High Reliability
- Avalanche Energy Rated
- RoHS Compliant

Applications

- · Switching Power Supplies
- · Power Switching Circuits
- General Purpose

Ordering Informations

Part Number	Package	Brand	
RHRP3060	TO-220AC-2L	RHRP3060	

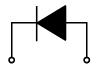
Description

The RHRP3060 is a hyperfast diode with soft recovery characteristics. It has the half recovery time of ultrafast diodes and is silicon nitride passivated ionimplanted epitaxial planar construction. These devices are intended to be used as freewheeling clamping diodes and diodes in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Pin Assignments



TO-220



1. Cathode 2. Anode

Absolute Maximum Ratings

Symbol	Parameter	RHRP3060	Unit
V _{RRM}	Peak Repetitive Reverse Voltage	600	V
V _{RWM}	Working Peak Reverse Voltage	600	V
V _R	DC Blocking Voltage	600	V
I _{F(AV)}	Average Rectified Forward Current (T _C = 120°C)	30	Α
I _{FRM}	Repetitive Peak Surge Current (Square Wave, 20KHz)	70	Α
I _{FSM}	Nonrepetitive Peak Surge Current (Halfwave, 1 Phase, 60Hz)	325	Α
P _D	Maximum Power Dissipation	125	W
E _{AVL}	Avalanche Energy (See Figures 10 and 11)	20	mJ
T _J , T _{STG}	Operating and Storage Temperature	-65 to 175	°C

Electrical Characteristics $T_C = 25$ °C unless otherwise noted

Symbol	Took Conditions	RHRP3060			11
	Test Conditions	Min.	Тур.	Max.	Unit
V _F	I _F = 30 A	-	-	2.1	V
	I _F = 30 A, T _C = 150°C	-	-	1.7	V
$I_{R} \qquad V_{R} = 400 \text{ V}$ $V_{R} = 600 \text{ V}$ $V_{R} = 400 \text{ V}, T_{C} = 150^{\circ}\text{C}$ $V_{R} = 600 \text{ V}, T_{C} = 150^{\circ}\text{C}$	V _R = 400 V	-	-	-	μΑ
	V _R = 600 V	-	-	250	μΑ
	V _R = 400 V, T _C = 150°C	-	-	-	mA
	V _R = 600 V, T _C = 150°C	-	-	1.0	mA
· ·	I _F = 1 A, dI _F /dt = 200 A/μs	-	-	40	ns
	I _F = 30 A, dI _F /dt = 200 A/μs	-	-	45	ns
t _a	I _F = 30 A, dI _F /dt = 200 A/μs	-	22	-	ns
t _b	I _F = 30 A, dI _F /dt = 200 A/μs	-	18	-	ns
Q _{RR}	I _F = 30 A, dI _F /dt = 200 A/μs	-	100	-	nC
CJ	V _R = 600 V, I _F = 0 A	-	85	-	pF
$R_{\theta JC}$		-	-	1.2	°C/W

DEFINITIONS

 V_F = Instantaneous forward voltage (pw = $300\mu s$, D = 2%)

 I_R = Instantaneous reverse current.

 t_{rr} = Reverse recovery time (See Figure 9), summation of t_a + t_b .

 t_a = Time to reach peak reverse current (See Figure 9).

 t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 9).

Q_{RR} = Reverse recovery charge.

C_J = Junction Capacitance.

 $R_{\theta JC}$ = Thermal resistance junction to case.

pw = pulse width.

D = Duty cycle.

Typical Performance Characteristics

Figure 1. Forward Current vs Forward Voltage

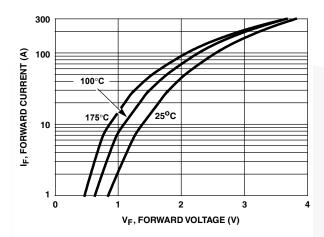


Figure 3. t_{rr}, t_a and t_b Curves vs Forward Current

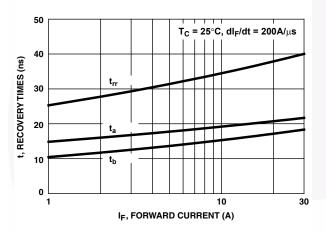


Figure 5. t_{rr}, t_a and t_b Curves vs Forward Current

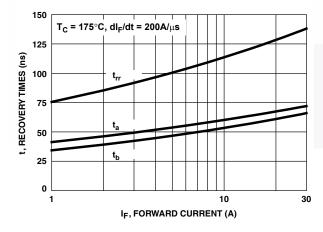


Figure 2. Reverse Currnt vs Reverse Voltage

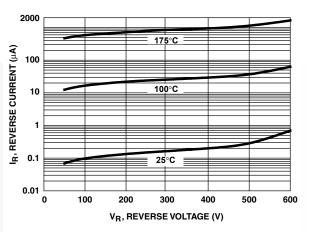


Figure 4. t_{rr}, t_a and t_b Curves vs Forward Current

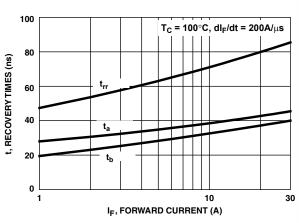
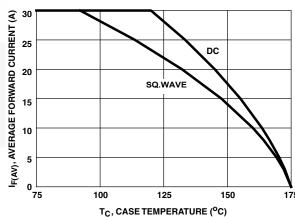
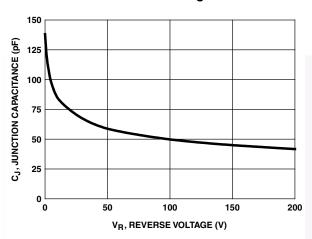


Figure 6. Current Derating Curve



Typical Performance Characteristics (Continued)

Figure 7. Junction Capacitance vs Reverse Voltage



Test Circuit and Waveforms

Figure 8. t_{rr} Test Circuit

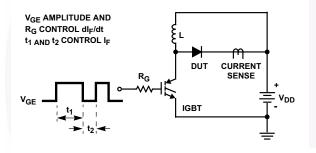


Figure 10. Avalanche Energy Test Circuit

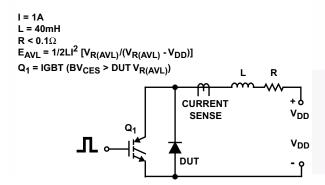


Figure 9. t_{rr} Waveforms and Definitions

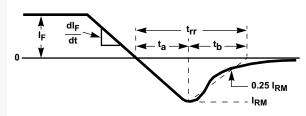
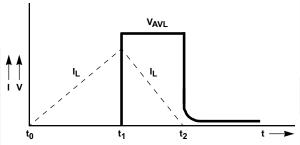
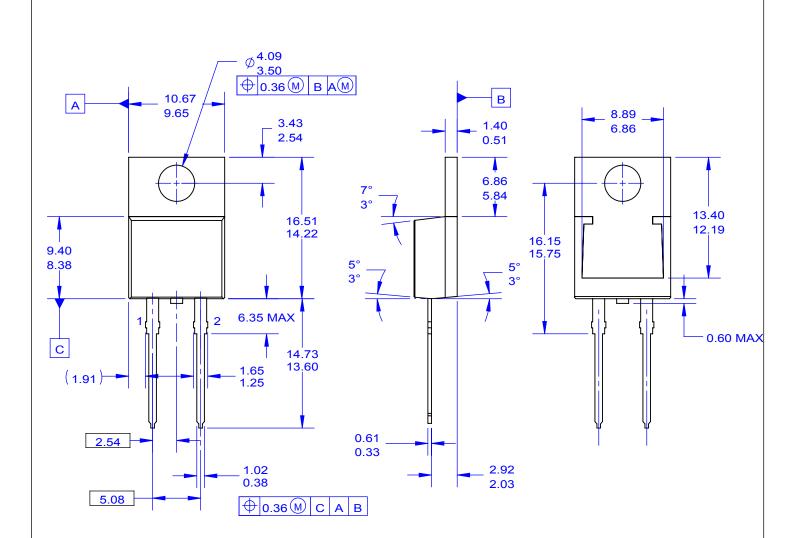
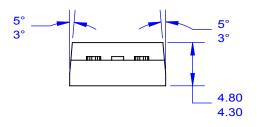


Figure 11. Avalanche Current and Voltage Waveforms









NOTES:

- A. PACKAGE REFERENCE: JEDEC TO220,ISSUE K, VARIATION AC,DATED APRIL 2002.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
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